

[PRECISION POLYSILICON RESISTOR PROCESS]

Abstract

A process is disclosed for fabricating precision polysilicon resistors which more precisely control the tolerance of the sheet resistivity of the produced polysilicon resistors. The process generally includes performing an emitter / FET activation rapid thermal anneal (RTA) on a wafer having partially formed polysilicon resistors, followed by steps of depositing a protective dielectric layer on the polysilicon, implanting a dopant through the protective dielectric layer into the polysilicon to define the resistance of the polysilicon resistors, and forming a silicide.